



THE DATASHEET OF AOI4T60P



General Description

- Trench Power AlphaMOS-II technology
- Low $R_{DS(ON)}$
- Low C_{iss} and C_{rss}
- High Current Capability
- RoHS and Halogen Free Compliant

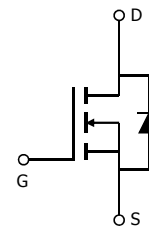
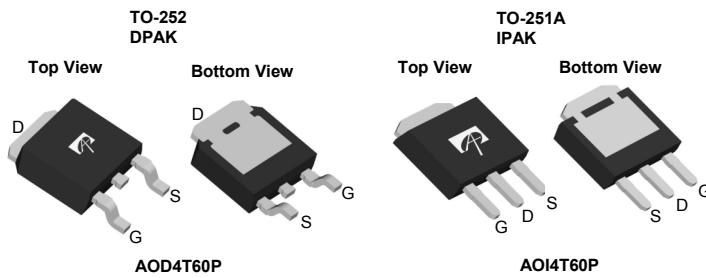
Applications

- General Lighting for LED and CCFL
- AC/DC Power supplies for Industrial, Consumer, and Telecom

Product Summary

$V_{DS} @ T_{j,max}$	700V
I_{DM}	16A
$R_{DS(ON),max}$	< 2.1 Ω
$Q_{g,typ}$	8.3nC
$E_{oss} @ 400V$	1.6 μ J

100% UIS Tested
 100% R_g Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOD4T60P	TO-252	Tape & Reel	2500
AOI4T60P	TO-251A	Tube	4000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	4
		$T_C=100^\circ\text{C}$	2.4
Pulsed Drain Current ^C	I_{DM}	16	A
Avalanche Current ^C $L=1\text{mH}$	I_{AR}	4	A
Repetitive avalanche energy ^C	E_{AR}	8	mJ
Single pulsed avalanche energy ^H	E_{AS}	203	mJ
MOSFET dv/dt ruggedness		50	V/ns
Peak diode recovery dv/dt	dv/dt	5	V/ns
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	83
		Derate above 25°C	0.7
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	T_L	300	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Units
Maximum Junction-to-Ambient ^{A,D}	$R_{\theta JA}$	40	50	$^\circ\text{C/W}$
Maximum Case-to-sink ^A	$R_{\theta CS}$	-	0.5	$^\circ\text{C/W}$
Maximum Junction-to-Case ^{D,F}	$R_{\theta JC}$	1.25	1.5	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC PARAMETERS							
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V, T _J =25°C	600			V	
		I _D =250μA, V _{GS} =0V, T _J =150°C		700			
BV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D =250μA, V _{GS} =0V		0.55		V/°C	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =600V, V _{GS} =0V			1	μA	
		V _{DS} =480V, T _J =125°C			10		
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±30V			±100	nA	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =5V, I _D =250μA	3	4.2	5	V	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =2A		1.75	2.1	Ω	
g _{FS}	Forward Transconductance	V _{DS} =40V, I _D =2A		3.2		S	
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.78	1	V	
I _S	Maximum Body-Diode Continuous Current				4	A	
I _{SM}	Maximum Body-Diode Pulsed Current ^C				16	A	
DYNAMIC PARAMETERS							
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =100V, f=1MHz		522		pF	
C _{oss}	Output Capacitance				22		pF
C _{o(er)}	Effective output capacitance, energy related ^I	V _{GS} =0V, V _{DS} =0 to 480V, f=1MHz		20		pF	
C _{o(tr)}	Effective output capacitance, time related ^J				32		pF
C _{rss}	Reverse Transfer Capacitance	V _{GS} =0V, V _{DS} =100V, f=1MHz		2		pF	
R _g	Gate resistance	f=1MHz		2.9		Ω	
SWITCHING PARAMETERS							
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =480V, I _D =4A		8.3	15	nC	
Q _{gs}	Gate Source Charge				3.4		nC
Q _{gd}	Gate Drain Charge				1.9		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =300V, I _D =4A, R _G =25Ω		21		ns	
t _r	Turn-On Rise Time				19		ns
t _{D(off)}	Turn-Off DelayTime				25		ns
t _f	Turn-Off Fall Time				11		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =4A, dI/dt=100A/μs, V _{DS} =100V		309		ns	
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =4A, dI/dt=100A/μs, V _{DS} =100V		2.7		μC	

A. The value of R_{qJA} is measured with the device in a still air environment with T_A=25° C.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C in a TO252 package, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C.

G. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

H. L=60mH, I_{AS}=2.6A, V_{DD}=150V, R_G=10Ω, Starting T_J=25° C.

I. C_{o(er)} is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}.

J. C_{o(tr)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}.

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

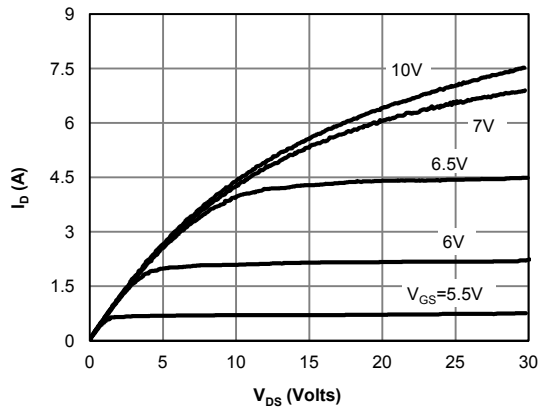


Figure 1: On-Region Characteristics

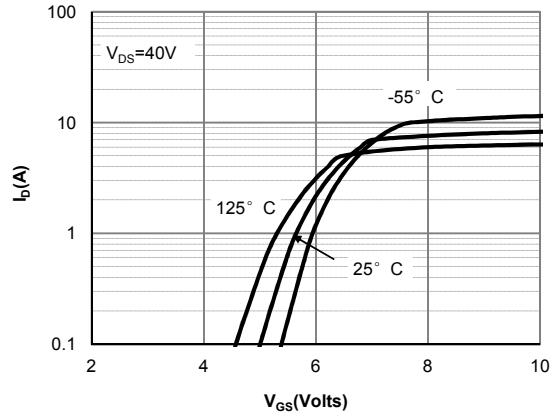


Figure 2: Transfer Characteristics

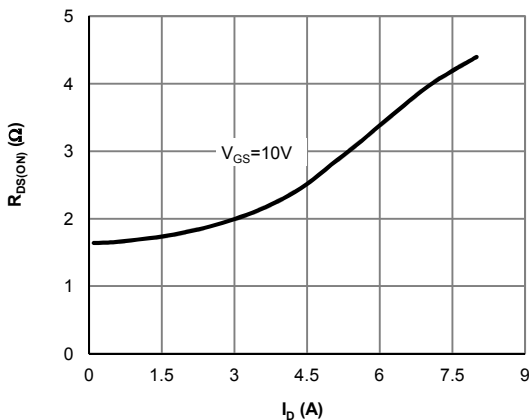


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

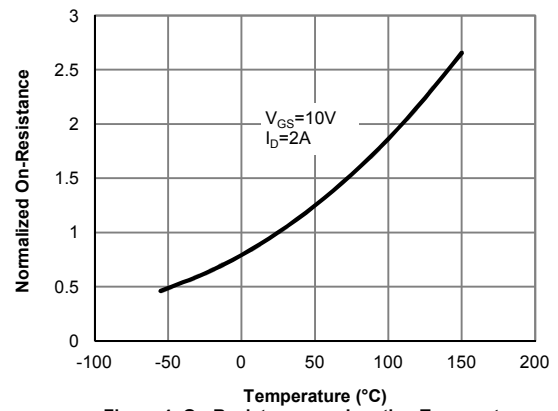


Figure 4: On-Resistance vs. Junction Temperature

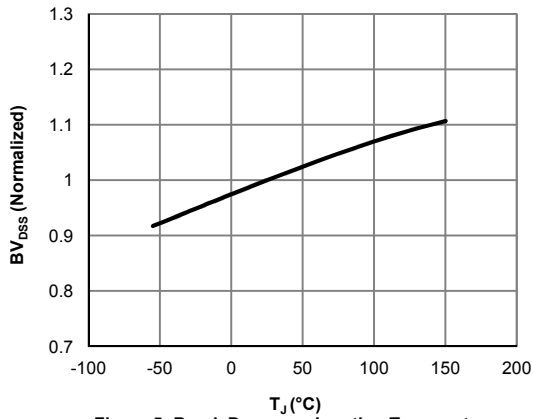


Figure 5: Break Down vs. Junction Temperature

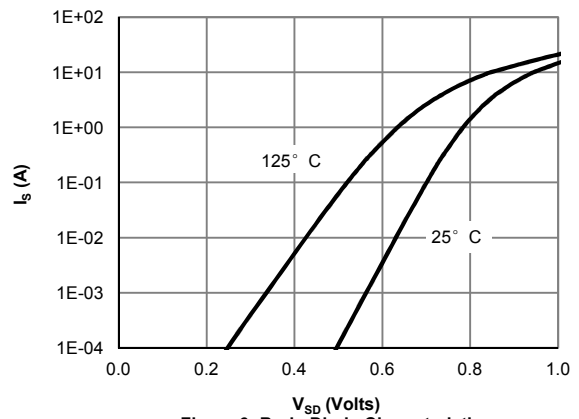


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

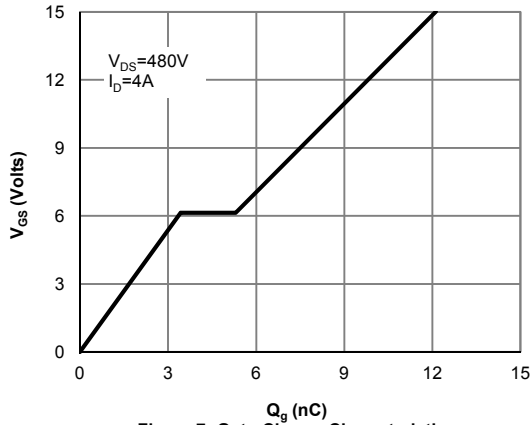


Figure 7: Gate-Charge Characteristics

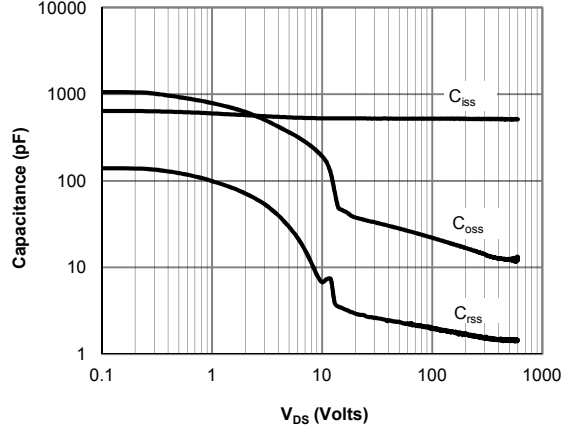


Figure 8: Capacitance Characteristics

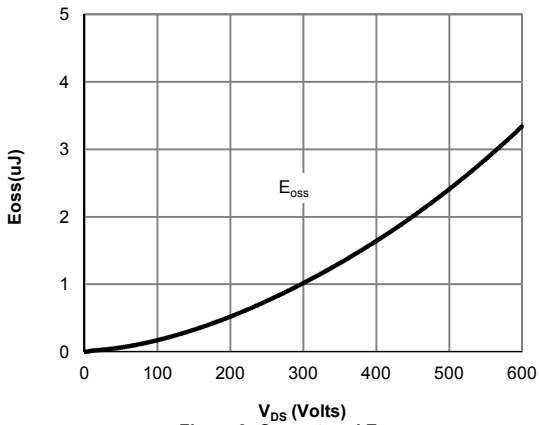


Figure 9: Coss stored Energy

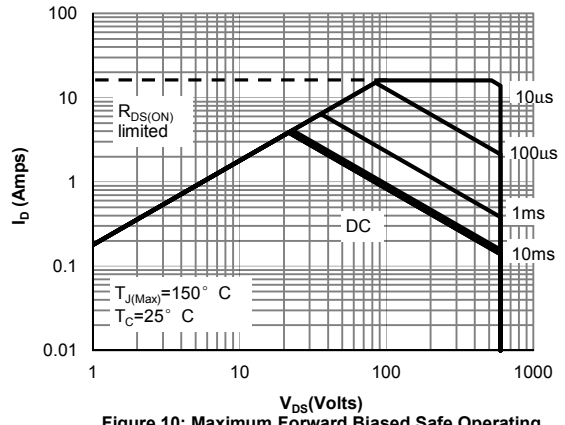


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

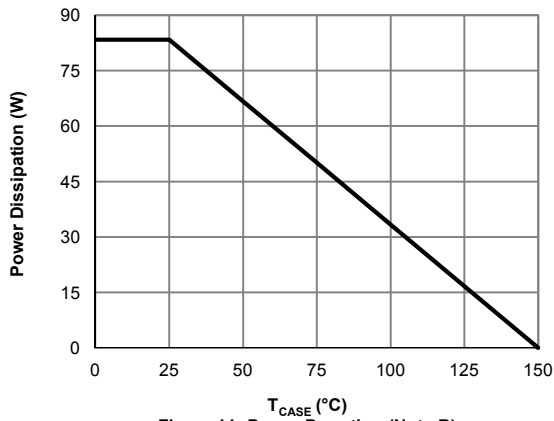


Figure 11: Power De-rating (Note B)

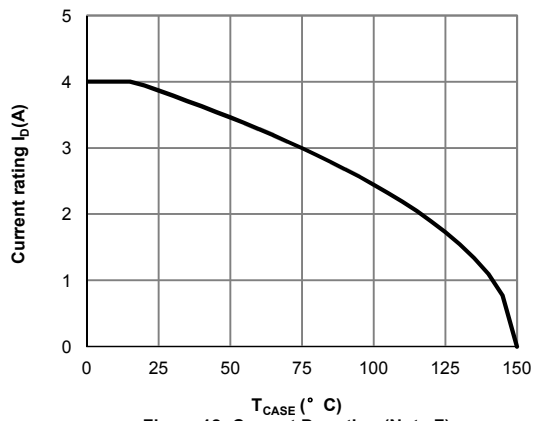


Figure 12: Current De-rating (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

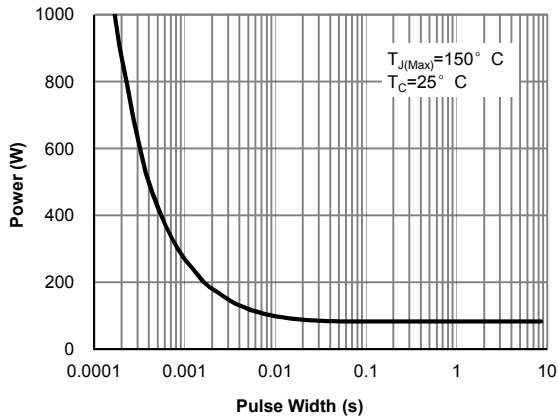


Figure 13: Single Pulse Power Rating Junction-to-Case (Note F)

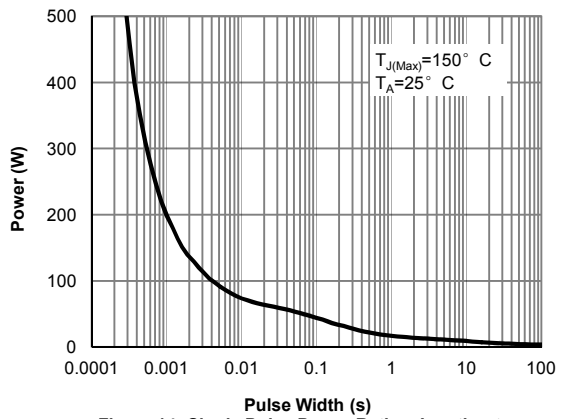


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note G)

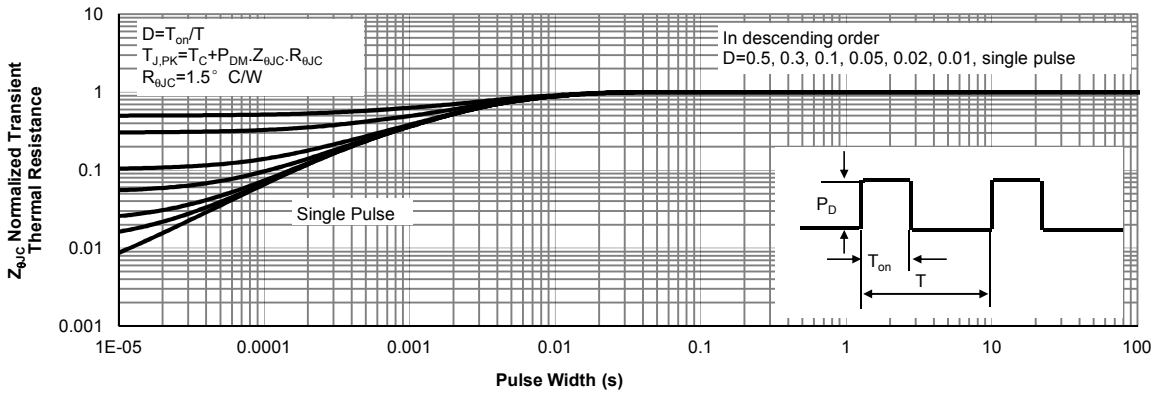


Figure 15: Normalized Maximum Transient Thermal Impedance (Note F)

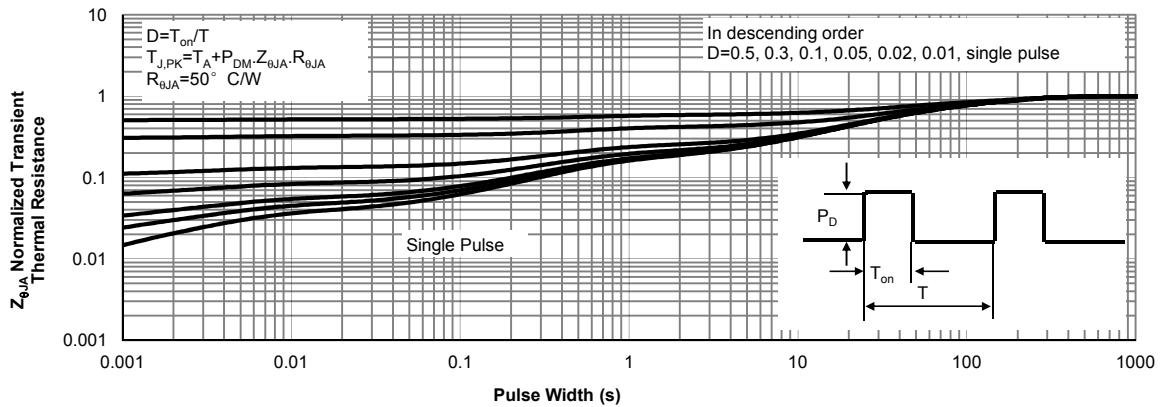
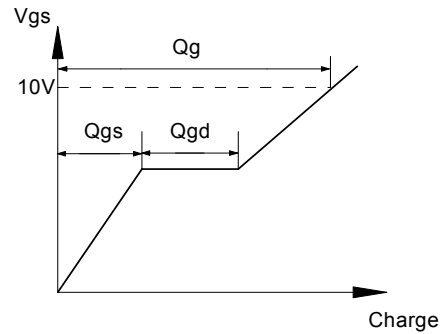
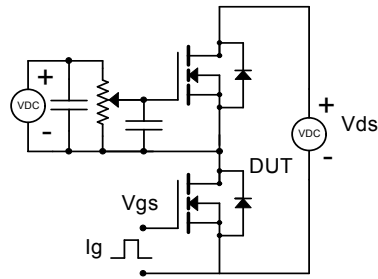
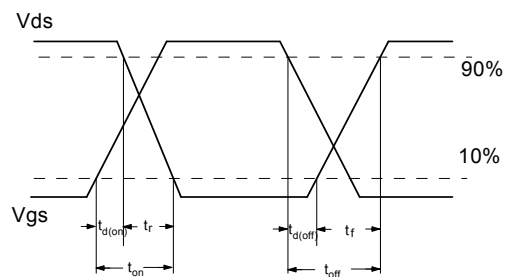
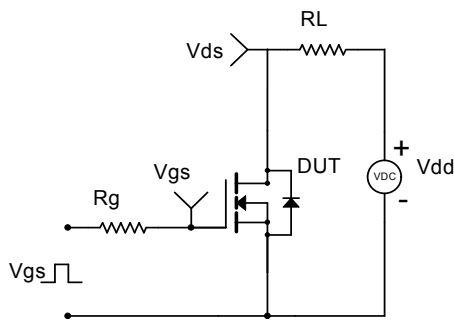


Figure 16: Normalized Maximum Transient Thermal Impedance (Note G)

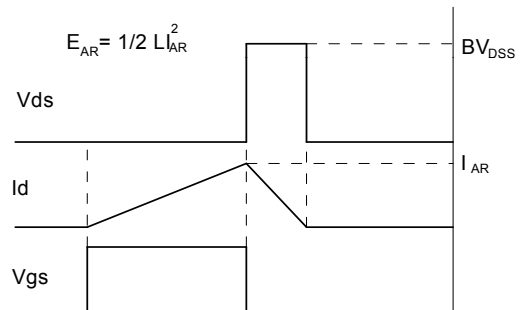
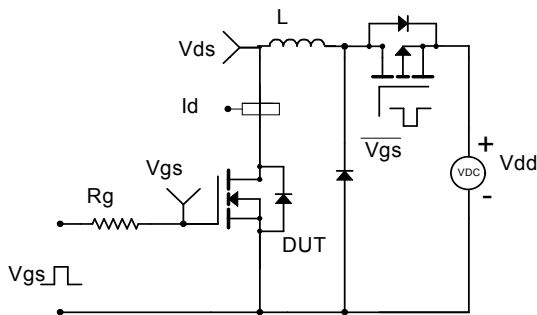
Gate Charge Test Circuit & Waveform



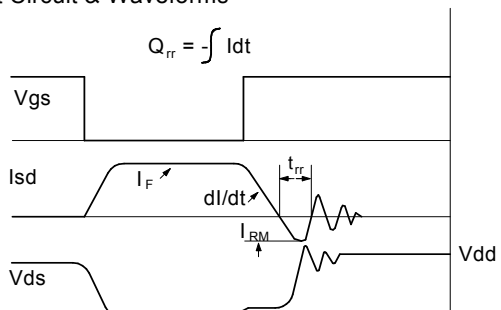
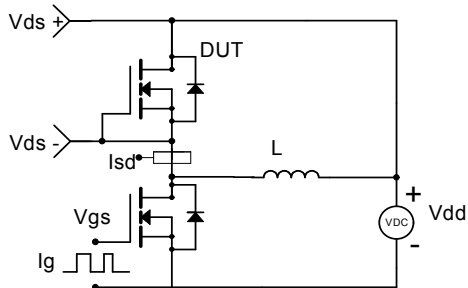
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

- ⊖ [View AOI4T60P on WIN SOURCE](#)
- ⊖ [Alpha & Omega Semiconductor Inc. Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

- ✓ Global Sourcing Solution
- ✓ Obsolete Management
- ✓ Cost Control Management
- ✓ Shortage Management
- ✓ Alternative Solution
- ✓ Excess Inventory Management